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Search Partnumber : Included a word "30N60";-Total : 243 (1/13 Page) Manufacturer: Part # Datasheet: Description: Infineon Technologies A... AIKW30N60CT 1Mb / 16P: Low Loss DuoPack: IGBT in TRENCHSTOP™ and Fieldstop technology with soft, fast recovery antiparallel Emitter Controlled diode V2.1 2017-02-09:

30N60 là gì, mua o dâu, giá bao nhiêu, thông so ky thuat, datasheet, so do chân, thay the tuong duong, cách su dung, ung dung Gio hàng 0 Gui yêu cau Tu van: 0979.466.469 / 0938.128.290 Email: cskh@dientutuonglai Dang nhap | Dang kí ...

FGH30N60LSD 3 ELECTRICAL CHARACTERISTICS OF THE IGBT (TC = 25°C unless otherwise noted) (continued) Parameter Symbol Test Conditions Min Typ Max Unit DYNAMIC CHARACTERISTICS Input Capacitance Cies VCE = 30 V, VGE = 0 V, f = 1 MHz - 3550 - pF Output Capacitance Coes - 245 - pF Reverse Transfer Capacitance Cres - 90 - ...

4 IKW30N60H3 High speed switching series third generation Rev. 2.2, 2014-03-12 Maximum ratings Parameter Symbol Value Unit Collector-emitter voltage, Tvj >= 25°C VCE 600 V DC collector current, limited by Tvjmax TC = 25°C TC = 100°C IC 60.0 30.0

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FCH35N60 2 ABSOLUTE MAXIMUM RATINGS (TC = 25°C unless otherwise noted) Symbol Parameter Value Unit VDSS Drain to Source Voltage 600 V VGSS Gate to Source Voltage ±30 V ID Drain Current - Continuous (TC = 25°C) 35 A - Continuous (TC = 100°C) 22.2 IDM Drain Current - Pulsed (Note 1) 105 A EAS Single Pulsed Avalanche Energy (Note 2) ...

The 30N60 designed as a 600V, 30A IGBT manufactured in a through-hole TO-247-3-21 package. 30N60 IGBT features low switching losses, high energy efficiency and high avalanche ruggedness for soft switching applications. ... Inverters; Household devices . Reviews (0) Reviews There are no reviews yet. Be the first to review "30N60 IGBT 600V 30A ...

Igbt Ngbt30n60flwg 30n60 30n60fl 30a/600v. Adicionar aos favoritos. 4.3 Avaliação 4.3 de 5. 3

Inverter 30n60

opiniões. (3) R\$ 25. Ver os meios de pagamento. ... ar condicionado inverter; bicicletas; cafeteira; carros novos; computador; fogão 4 boca; fone de ouvido bluetooth; freezer vertical; geladeira frost free; guarda roupa casal; guarda roupa solteiro ...

HGTG30N60A4D 3 ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)
(continued) Parameter Symbol Test Condition Min Typ Max Unit Thermal Resistance Junction To Case R_{JC}
IGBT - - 0.27 °C/W Diode - - 0.65 °C/W

The HGTG30N60A4D is a MOS gated high voltage switching devices combining the best features of MOSFETs and bipolar transistors. This device has the high input impedance of a MOSFET ...

0.2. Size:157K 1 hgtg20n60b3d.pdf S E M I C O N D U C T O R HGTG20N60B3D40A, 600V, UFS Series N-Channel IGBT with Anti-Parallel Hyperfast Diode January 1996 Features Package 40A, 600V at T_C = +25°C JEDEC STYLE TO-247 Typical Fall Time - 140ns at +150°C E_{CEC} Short Circuit Rated G Low Conduction Loss Hyperfast Anti-Parallel Diode Description The HGTG20N60B3D ...

- Inverter NPT-Technology for 600V applications offers: - very tight parameter distribution - high ruggedness, temperature stable behaviour - parallel switching capability Very soft, fast recovery anti-parallel Emitter Controlled Diode Pb-free lead plating; RoHS compliant Qualified according to JEDEC1 for target applications

Order today, ships today. IGW30N60H3FKSA1 - IGBT Trench Field Stop 600 V 60 A 187 W Through Hole PG-TO247-3-1 from Infineon Technologies. Pricing and Availability on millions of electronic components from Digi-Key Electronics.

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SGP30N60 SGW30N60Fast IGBT in NPT-technology C 75% lower E_{off} compared to previous generation combined with low conduction losses Short circuit withstand time 10 s GE ...

HGTG30N60A4 2 ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)
Parameter Symbol Ratings Unit Collector to Emitter Voltage BV_{CES} 600 V Collector Current Continuous T_C = 25°C I_C 75 A T_C = 110°C 60 A Collector Current Pulsed (Note 1) I_{CM} 240 A Gate to Emitter Voltage Continuous V_{GES} 17.20 V Gate to Emitter Voltage Pulsed ...

..1. Size:361K infineon sgp30n60 sgw30n60 rev2 5g.pdf SGP30N60 SGW30N60Fast IGBT in NPT-technology C 75% lower E_{off} compared to previous generation combined with low conduction losses Short circuit withstand time 10 s GE Designed for: - Motor controls - Inverter NPT-Technology for 600V applications offers: - very tight parameter distribution - high ...

HGTG30N60B3 3 ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^{\circ}\text{C}$ unless otherwise noted) (continued) Symbol Parameter Test Conditions Min. Typ. Max. Unit $T_d(\text{on})$ I Current Turn-On Delay Time IGBT and Diode at $T_J = 25^{\circ}\text{C}$ $I_{CE} = I_{C110}$ $V_{CE} = 0.8 V_{CES}$ $V_{GE} = 15\text{ V}$ $R_G = 3\text{ }\Omega$ $d(\text{off})$ I $L = 1\text{ mH}$ Test Circuit (Figure 17)

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